UNISONIC TECHNOLOGIES CO., LTD

UTG5N65-S

Preliminary

Insulated Gate Bipolar Transistor

650V TRENCH GATE FIELD-STOP IGBT

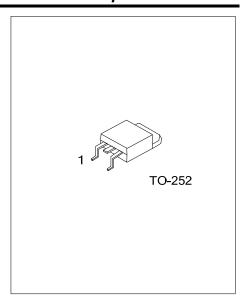
■ DESCRIPTION

The UTC **UTG5N65-S** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

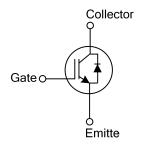
The UTC **UTG5N65-S** is suitable for the resonant or soft switching applications.



- * High switching speed
- * High avalanche ruggedness
- * Low saturation voltage: $V_{CE(SAT),Typ.}$ =1.46V @ Ic=5.0A, V_{GE} =15V (T_C =25°C)



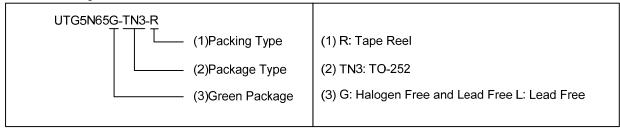
■ SYMBOL



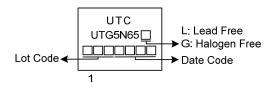
ORDERING INFORMATION

Ordering Number		Daalaaaa	Pin Assignment			Da alsisas	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTG5N65L-TN3-R	UTG5N65G-TN3-R	TO-252	G	С	E	Tape Reel	

Note: Pin Assignment: G: Gate C: Collector E: Emitter



■ MARKING



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■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V _{CES}	650	V
Gate-Emitter Voltage		\ <u>/</u>	±20	V
Transient Gate-emitter voltage (tp < 5 ms)		V_{GES}	±25	V
Continuous Collector Current	T _C =25°C	Ic	10	Α
	T _C =100°C		5	Α
Collector Current Pulsed (Note 1)		I _{CM}	20	Α
Die de Femurand Comment	T _C =25°C	l _F	10	Α
Diode Forward Current	T _C =100°C		5	Α
Short Circuit Withstand Time $V_{GE} = 15V, V_{CC} \le 200V$		tsc		
				μs
Allowed number of short circuits < 1000			3	
Time between short circuits: ≥1.0s T _{VJ} = 25°C				
Power Dissipation (T _C =25°C)		P _D	38	W
Operating Junction Temperature		T_J	-40 ~ +175	°C
Storage Temperature Range		T _{STG}	-55 ~ +175	°C

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	θјс	3.289	°C/W

^{2.} Pulse width limited by maximum junction temperature.

■ ELECTRICAL CHARACTERISTICS (Tc=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS			TYP	MAX	UNIT
Off Characteristics							
Collector-Emitter Breakdown Voltage	BV _{CES}			650			V
Collector Cut-Off Current	I _{CES}	V _{CE} =650V, V _{GE} =0V				5	μΑ
G-E Leakage Current	I _{GES}	V _{CE} =0V, V _{GE} =±20V				±100	nΑ
On Characteristics							
Gate to Emitter Threshold Voltage	$V_{GE(TH)}$	Ic=250µA, VcE=VGE		4.0		6.5	>
	V _{CE(SAT)}	1 5 0 0 1/ 45 1/	T _C =25°C		1.46	2.1	V
Collector to Emitter Saturation Voltage		Ic=5.0A, V _{GE} =15V	T _C =125°C		1.9		V
Dynamic Characteristics							
Input Capacitance	CIES	V _{CE} =25V, V _{GE} =0V, f=1MHz			511		pF
Output Capacitance	Coes				34		pF
Reverse Transfer Capacitance	Cres				9.1		рF
Switching Characteristics				-	-		
Total Gate Charge	\mathbf{Q}_{G}				45.4		nC
Gate-Emitter Charge	Q_{GE}	V _{CE} =520V, I _C =5.0A, V _{GE} =15V			14.8		nC
Gate-Collector Charge	Q _{GC}				18.8		nC
Turn-On Delay Time	t _{DON)}				16		ns
Rise Time	t_{R}				22		ns
Turn-Off Delay Time	t _{DOFF)}	V _{CC} =400V, I _C =5.0A, R _G =5Ω, V _{GE} =0~15V, L=1000μH			45		ns
Fall Time	t _F				220		ns
Turn-On Switching Loss	Eon				0.197		mJ
Turn-Off Switching Loss	Eoff				0.151		mJ
SOURCE- DRAIN DIODE RATINGS AN	D CHARACTE	RISTICS					
Forward Voltage Drop	V _F	I _F =5.0A			1.55	3.0	V
Reverse Recovery Time	t _{rr}	I _F =5.0A, dI/dt=100A/μS,			40		ns
Reverse Recovery Charge	Qrr	V _{CC} =400V			14		nC

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